

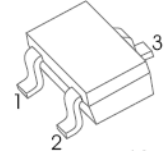
# SS8550

TRANSISTOR (PNP)

## FEATURES

- High Collector Current
- Complementary to SS8050

SOT - ' 23



1. BASE
2. EMITTER
3. COLLECTOR

## MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	-40	V
V <sub>CEO</sub>	Collector-Emitter Voltage	-25	V
V <sub>EBO</sub>	Emitter-Base Voltage	-5	V
I <sub>C</sub>	Collector Current	-1.5	A
P <sub>C</sub>	Collector Power Dissipation	∅0	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	∧ Ĝ	°C/W
T <sub>j</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature	-55~+150	°C

## ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)

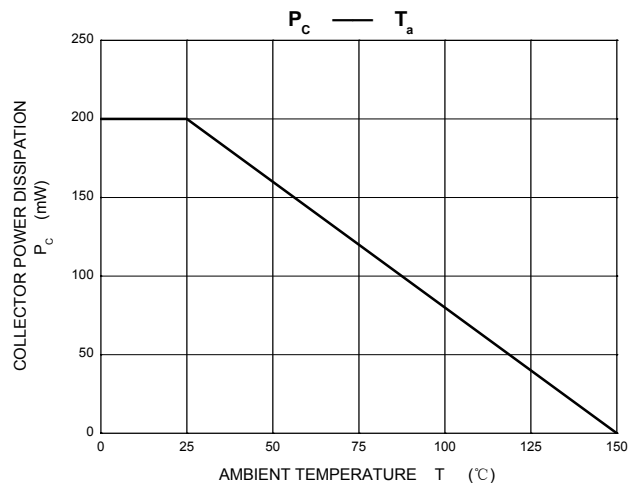
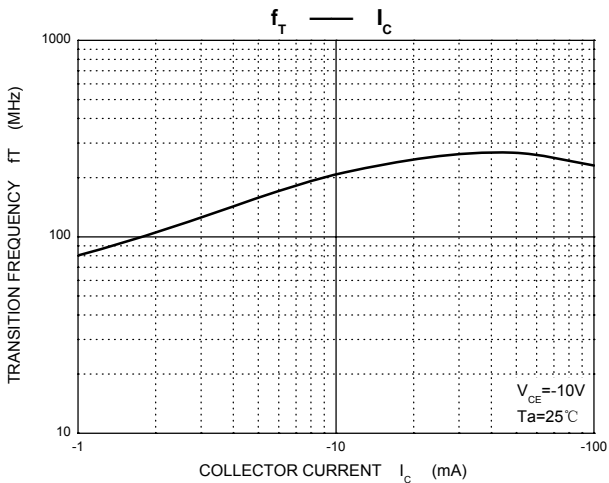
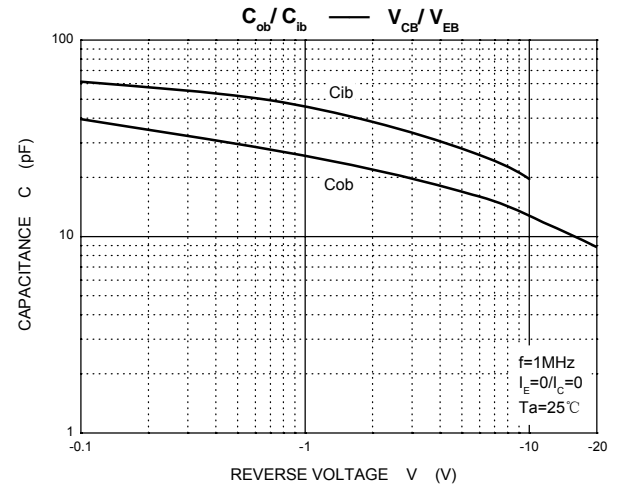
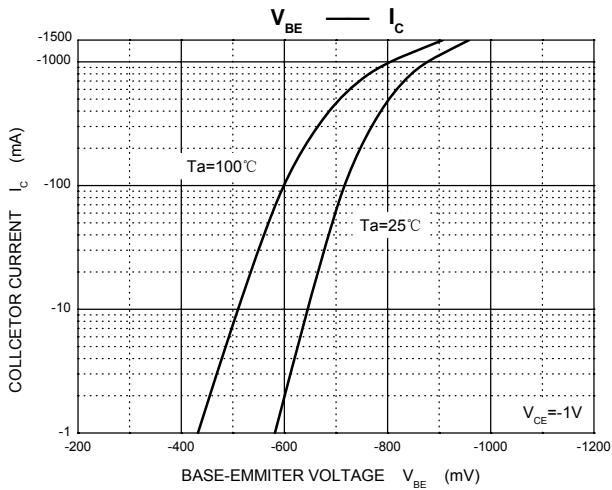
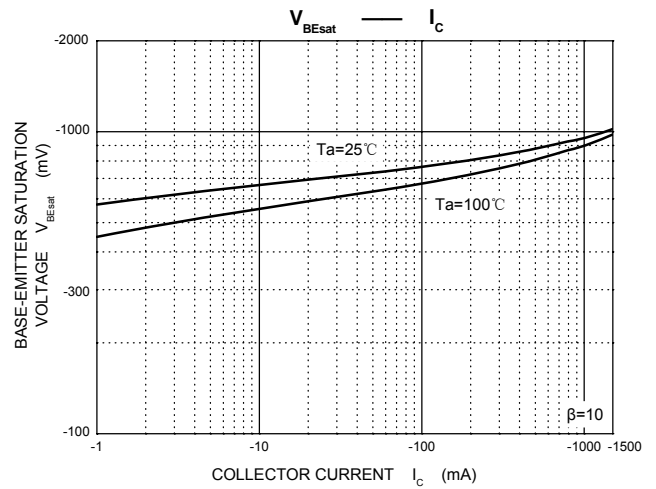
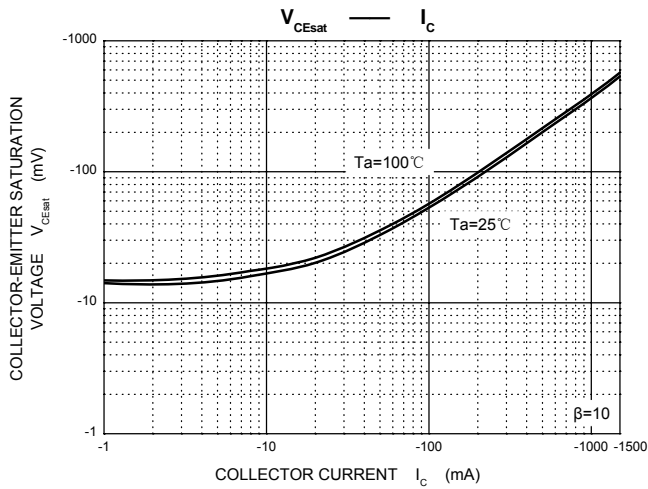
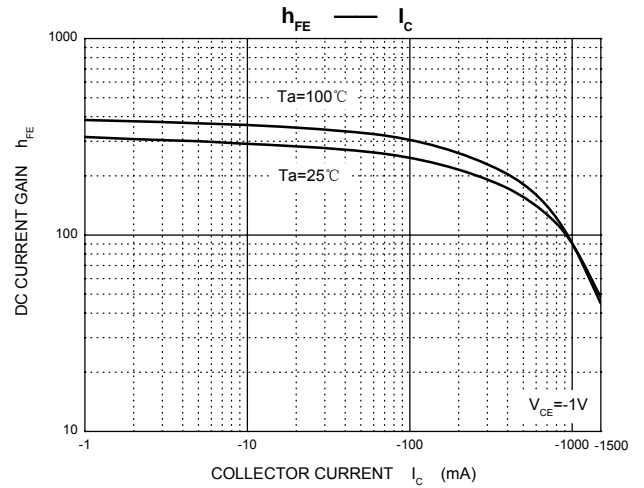
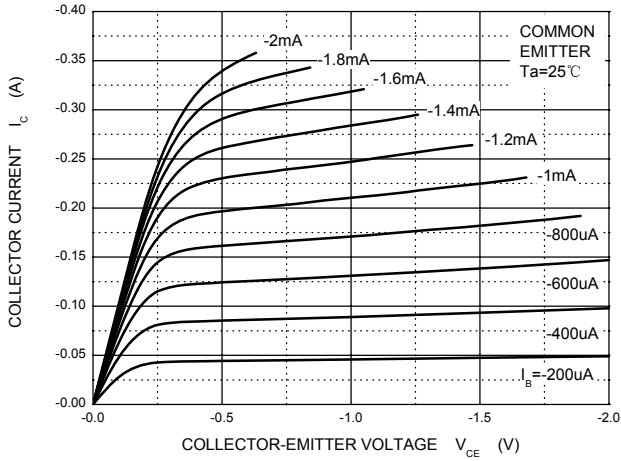
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =-100μA, I <sub>E</sub> =0	-40			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =-0.1mA, I <sub>B</sub> =0	-25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =-100μA, I <sub>C</sub> =0	-5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =-40V, I <sub>E</sub> =0			-100	nA
Collector cut-off current	I <sub>CEO</sub>	V <sub>CE</sub> =-20V, I <sub>B</sub> =0			-100	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =-5V, I <sub>C</sub> =0			-100	nA
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-100mA	120		400	
	h <sub>FE(2)</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-800mA	40			
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA			-0.5	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =-800mA, I <sub>B</sub> =-80mA			-1.2	V
Base-emitter voltage	V <sub>BE</sub>	V <sub>CE</sub> =-1V, I <sub>C</sub> =-10mA			-1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =-10V, I <sub>C</sub> =-50mA, f=30MHz	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =-10V, I <sub>E</sub> =0, f=1MHz			20	pF

## CLASSIFICATION OF h<sub>FE(1)</sub>

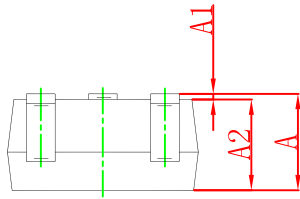
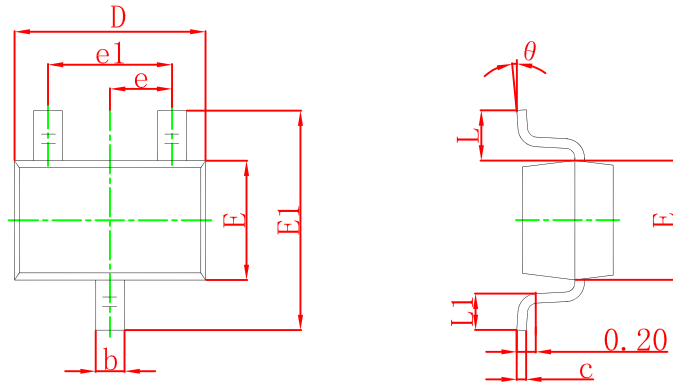
RANK	L	H	J
RANGE	120 - 200	200 - 350	300 - 400
MARKING	Y2		

# Typical Characteristics

Static Characteristic

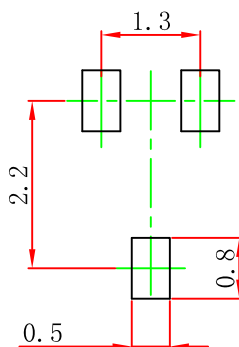


## SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

## SOT-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance:  $\pm 0.05$  mm.
3. The pad layout is for reference purposes only.

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